

# **ISC Silicon NPN Power Transistor**

#### **DESCRIPTION**

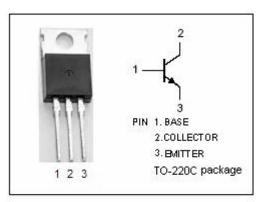
- · Low Collector Saturation Voltage
- · Good Linearity of hFE
- · High Switching Speed
- Complement to Type 2SA1289
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

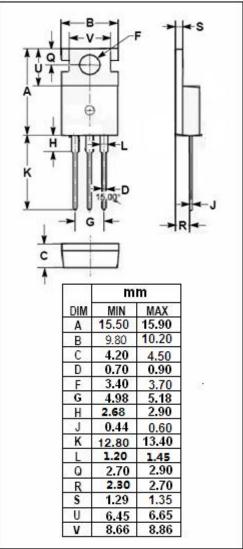
### **APPLICATIONS**

- · Various inductance lamp drivers for electrical equipment
- Inverters, converters
- Power amplifier
- Switching regulator, dirver

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>СВО</sub>	Collector-Base Voltage	80	V	
$V_{\text{CEO}}$	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	5	Α	
I <sub>CM</sub>	Collector Current-Pulse	7	Α	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	30	W	
TJ	T <sub>J</sub> Junction Temperature		°C	
T <sub>stg</sub>	T <sub>stg</sub> Storage Temperature Range		$^{\circ}\!\mathbb{C}$	





## isc Silicon NPN Power Transistor

2SC3253

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
$V_{(\text{BR})\text{CEO}}$	Collector-Emitter Breakdown Voltage	$I_C$ = 1mA; $R_{BE}$ = $\infty$	60			V	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	80			V	
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5			V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic= 2.5A; I <sub>B</sub> = 0.125A			0.4	V	
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			100	μА	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			100	μА	
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	70		280		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> =1A; V <sub>CE</sub> = 5V		100		MHz	
Switching times							
t <sub>on</sub>	Turn-on Time			0.1		μS	
t <sub>stg</sub>	Storage Time	$I_{C}$ = 2A; $I_{B1}$ = $-I_{B2}$ = 0.1A; $R_{L}$ = 10 $\Omega$ ; $V_{CC}$ = 20V		0.5		μS	
t <sub>f</sub>	Fall Time			0.1		μS	

### ♦ h<sub>FE</sub> Classifications

Q	R	S
70-140	100-200	140-280

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